WNSC2D30650CW



Rev.01 - 16 December 2021

Product data sheet

1. General description

WeEn Semi

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
 - Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

| Table 1. Q | uick reference data | | | | | | |
|--------------------|---------------------------------|---|--------|-------------|------|------|----|
| Symbol | Parameter | Conditions | Values | | | Unit | |
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 650 | | | V |
| I _{O(AV)} | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 117 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | | 30 | | А | |
| Tj | junction temperature | | 175 | | °C | | |
| Symbol | Parameter | Conditions | | Min Typ Max | | Unit | |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | $I_F = 15 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$ | | - | 1.45 | 1.7 | V |
| | | I_{F} = 15 A; T_{j} = 150 °C; per diode; <u>Fig. 5</u> | | - | 1.65 | 1.9 | V |
| Dynamic | characteristics | | | | | | |
| Q _r | recovered charge | $I_F = 15 \text{ A}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ per diode}; \text{ Fig. 7}$ | | - | 24 | - | nC |

5. Pinning information

| Table 2. Pinning information | | | | | | | | |
|------------------------------|--------|-------------------------------------|--------------------|----------------|--|--|--|--|
| Pin | Symbol | Description | Simplified outline | Graphic symbol | | | | |
| 1 | A1 | anode | | | | | | |
| 2 | К | cathode | | | | | | |
| 3 | A2 | anode | | <u> </u> | | | | |
| mb | mb | mounting base; connected to cathode | | sym125 | | | | |

6. Ordering information

| Table 3. Ordering information | | | | | | | | |
|-------------------------------|---------|-----------------------|---------|---------------|---------|-------------|--|--|
| Type number | Package | Orderable part number | Packing | Small packing | Package | Package | | |
| | name | | method | quantity | version | issue date | | |
| WNSC2D30650CW | TO247 | WNSC2D30650CWQ | Tube | 30 | SOT429 | 25-Mar-2013 | | |

7. Marking

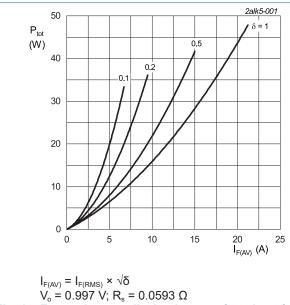
| Table 4. Marking codes | | | | | | |
|------------------------|-------------------|--|--|--|--|--|
| Type number | Marking codes | | | | | |
| WNSC2D30650CW | WNSC2D 30650CW | | | | | |

8. Limiting values

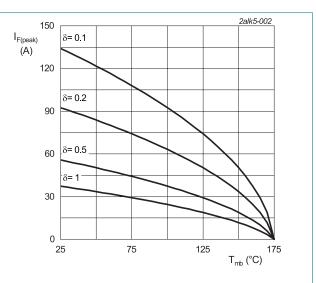
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|--------------------|--|--|------------|------------------|
| V _{RRM} | repetitive peak reverse voltage | | 650 | V |
| V _{RWM} | crest working reverse voltage | | 650 | V |
| V _R | reverse voltage | DC | 650 | V |
| I _{O(AV)} | average forward current | $δ = 0.5$; square-wave pulse; $T_{mb} \le 117$ °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | 30 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 123 °C; square-wave pulse; per diode | 30 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | 85 | A |
| | | t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode | 900 | A |
| l ² t | l ² t for fusing | sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms | 36 | A ² s |
| T _{stg} | storage temperature | | -55 to 175 | °C |
| Tj | junction temperature | | 175 | °C |



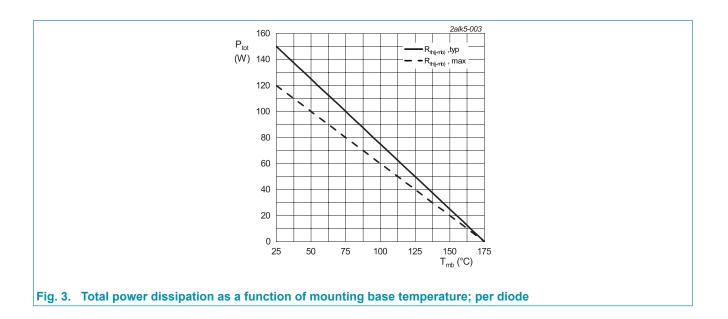
V_o = 0.997 V; R_s = 0.0593 Ω
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



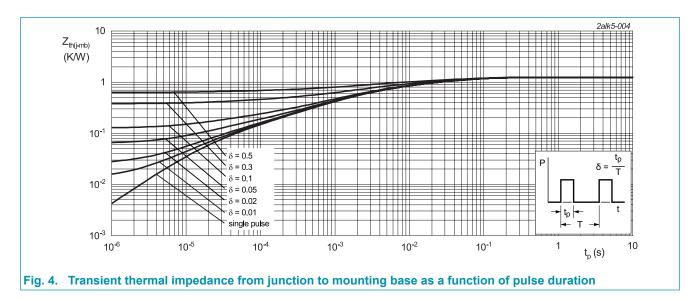


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WNSC2D30650CW Silicon Carbide Diode

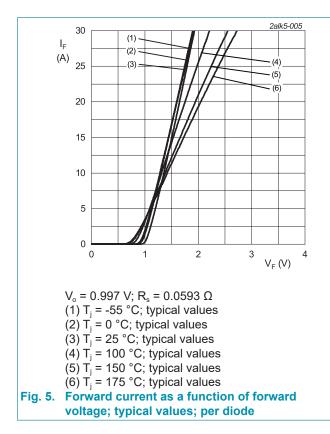


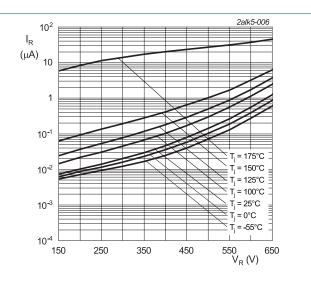
| Table 6. Th | ermal characteristics | | | | | |
|-----------------------|--|--------------------------|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| $R_{\text{th(j-mb)}}$ | thermal resistance | per diode; <u>Fig. 4</u> | - | 1 | 1.25 | K/W |
| | from junction to mounting base | both diodes conducting | - | - | 0.7 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 40 | - | K/W |



10. Characteristics

| Table 7. Cl | haracteristics | | | | | |
|-----------------|------------------------------------|---|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _F | forward current | $I_{F} = 15 \text{ A}; T_{j} = 25 \text{ °C}; \text{ per diode}; Fig. 5$ | - | 1.45 | 1.7 | V |
| | | $I_F = 15 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 5$ | - | 1.65 | 1.9 | V |
| | | $I_F = 15 \text{ A}; T_j = 175 \text{ °C}; \text{ per diode}; Fig. 5$ | - | 1.72 | 2.1 | V |
| I _R | reverse current | $V_{R} = 650 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ per diode}; \text{Fig. 6}$ | - | 3 | 50 | μA |
| | | V_{R} = 650 V; T _j = 175 °C; per diode; <u>Fig. 6</u> | - | 18 | 200 | μA |
| Dynamic | characteristics | | | | | |
| Qr | recovered charge | $I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$ | - | 24 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V_R = 1 V; T_j = 25 °C; per diode | - | 500 | - | pF |
| | | f = 1 MHz; V_R = 300 V; T_j = 25 °C; per diode | - | 58 | - | pF |
| | | f = 1 MHz; V_R = 600 V; T_j = 25 °C; per diode | - | 52 | - | pF |
| E _{as} | non-repetitive avalanche energy | $I_R = 6.3 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C};$ per diode | 99 | - | - | mJ |

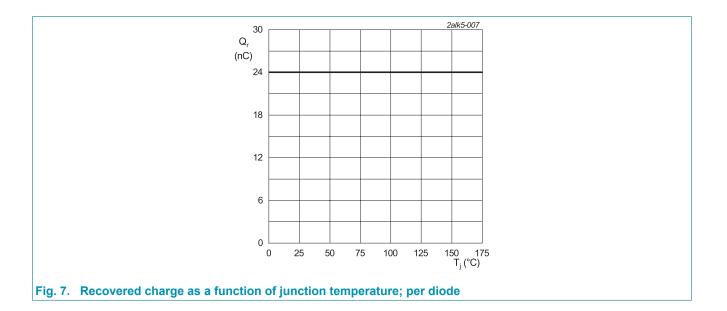






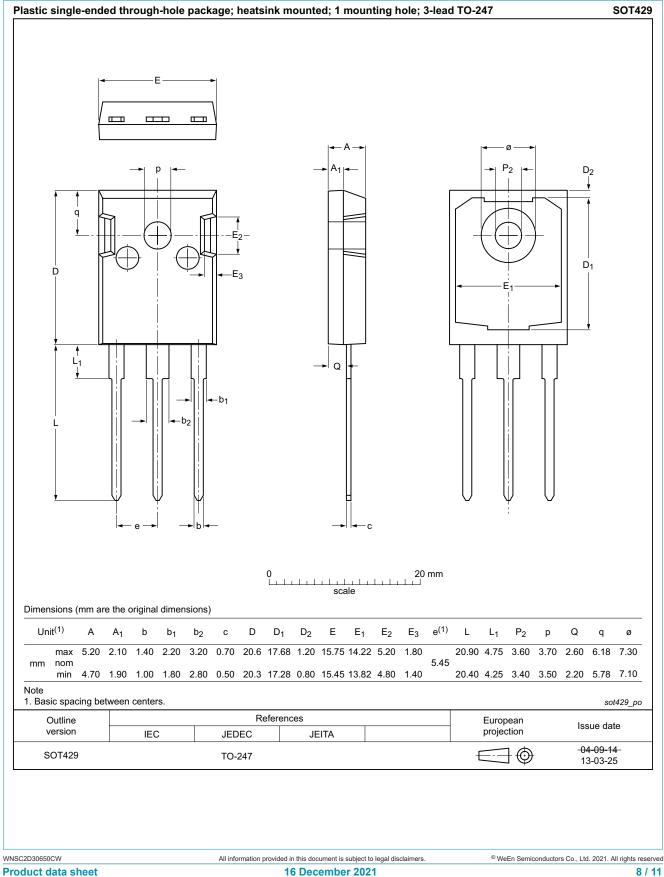
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Silicon Carbide Diode



WNSC2D30650CW Silicon Carbide Diode

11. Package outline



WNSC2D30650CW

12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

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